Product Summary

RoHS

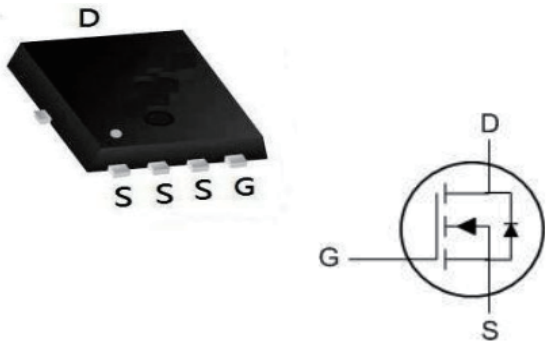
- ★ Green Device Available
- ★ Fast Switching Speed
- ★ 100% EAS Guaranteed
- ★ Advanced Trench MOS Technology

BVDSS	RDSON	ID
40V	6.9mΩ	60A

Applications

- ★ High Frequency Switching and Synchronous Rectification.
- ★ DC/DC Converter.

PDFN3X3 Pin Configuration



Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	40	V
V_{GS}	Gate-Source Voltage	±20	V
I_D@T_C=25℃	Continuous Drain Current[1]	60	A
I_D@T_C=100℃	Continuous Drain Current[1]	35	A
I_{DM}	Pulsed Drain Current[2]	130	A
EAS	Single Pulse Avalanche Energy[3]	48	mJ
I_{AS}	Avalanche Current	35	A
Pd@Tc=25℃	Total Power Dissipation[4]	39	W
T_{STG}	Storage Temperature Range	-55 to 150	℃
T_J	Operating Junction Temperature Range	-55 to 150	℃

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-ambient (Steady State)[1]	---	60	℃/W
$R_{\theta JC}$	Thermal Resistance Junction-Case[1]	---	3.2	℃/W

Electrical Characteristics (T_J =25 °C unless otherwise specified)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V , I_D=250uA	40	---	---	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance2	V_{GS}=10V , I_D=12A	---	6.9	8.5	mΩ
		V_{GS}=4.5V , I_D=10A	---	10	15	
$V_{GS(th)}$	Gate Threshold Voltage	V_{GS}=V_{DS} , I_D =250uA	1.35	---	3	V
I_{DSS}	Drain-Source Leakage Current	V_{DS}=32V , V_{GS}=0V , T_J=25℃	---	---	1	uA
		V_{DS}=32V , V_{GS}=0V , T_J=55℃	---	---	5	
I_{GSS}	Gate-Source Leakage Current	V_{GS}=±20V , V_{DS}=0V	---	---	±100	nA
R_g	Gate Resistance	V_{DS}=0V , V_{GS}=0V , f=1MHz	---	1.7	---	Ω
Q_g	Total Gate Charge (4.5V)	V_{DS}=20V , V_{GS}=4.5V , I_D=12A	---	5.8	---	nC
Q_{gs}	Gate-Source Charge		---	3	---	
Q_{gd}	Gate-Drain Charge		---	1.2	---	
$T_{d(on)}$	Turn-On Delay Time	V_{DD}=15V , V_{GS}=10V , R_G=3.3Ω I_D=1A	---	14.3	---	ns
T_r	Rise Time		---	5.6	---	
$T_{d(off)}$	Turn-Off Delay Time		---	20	---	
T_f	Fall Time		---	11	---	
C_{iss}	Input Capacitance	V_{DS}=15V , V_{GS}=0V , f=1MHz	---	690	---	pF
C_{oss}	Output Capacitance		---	193	---	
C_{rss}	Reverse Transfer Capacitance		---	38	---	

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current1,5	V_G=V_D=0V , Force Current	---	---	60	A
V_{SD}	Diode Forward Voltage2	V_{GS}=0V , I_S=1A , T_J=25℃	---	---	1	V

Notes:
1.The data tested by surface mounted on a 1 inch2 FR-4 board with 2OZ copper.
2.The data tested by pulsed , pulse width ≦ 300us , duty cycle ≦ 2%
3.The EAS data shows Max. rating . The test condition is V_{DD}=25V,V_{GS}=10V,L=0.1mH,IAS=31A
4.The power dissipation is limited by 150°C junction temperature
5.The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.

Typical Electrical and Thermal Characteristics (Curves)

Figure1: Output Characteristics

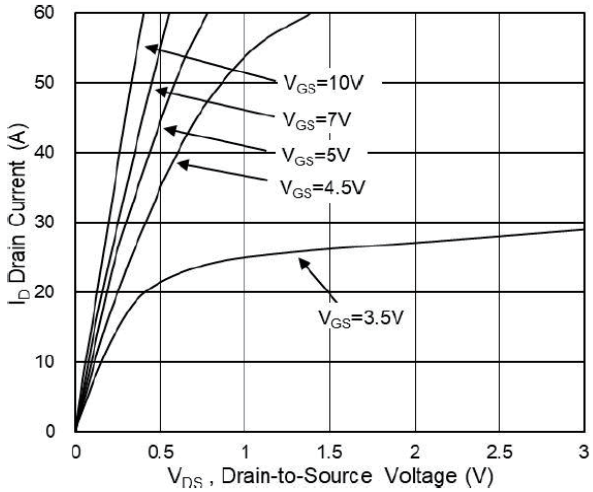


Figure 2: On-Resistance vs G-S Voltage

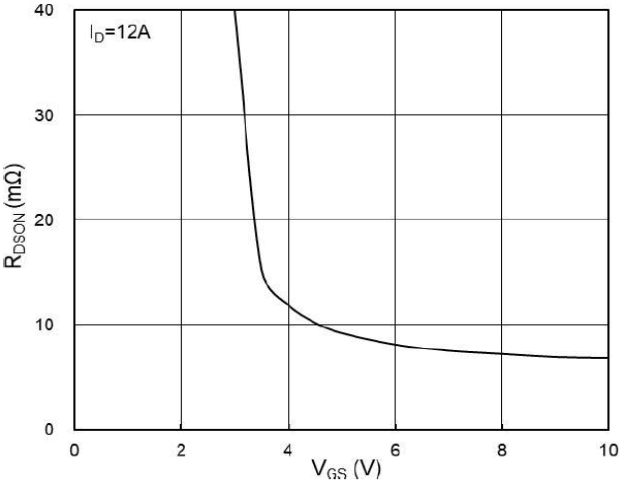


Figure 3:Source Drain Forward Character

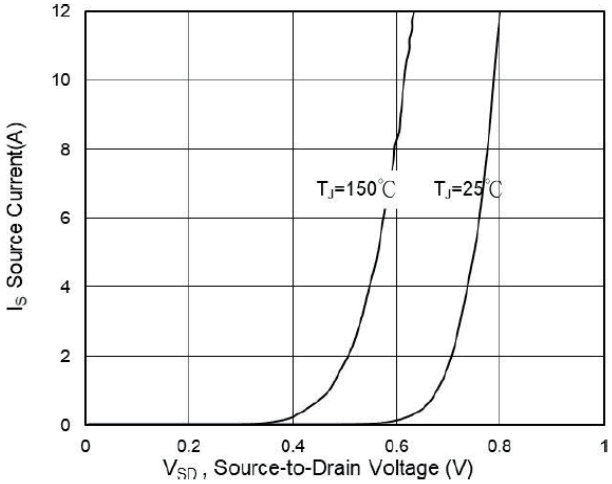


Figure 4: Gate-Charge Characteristics

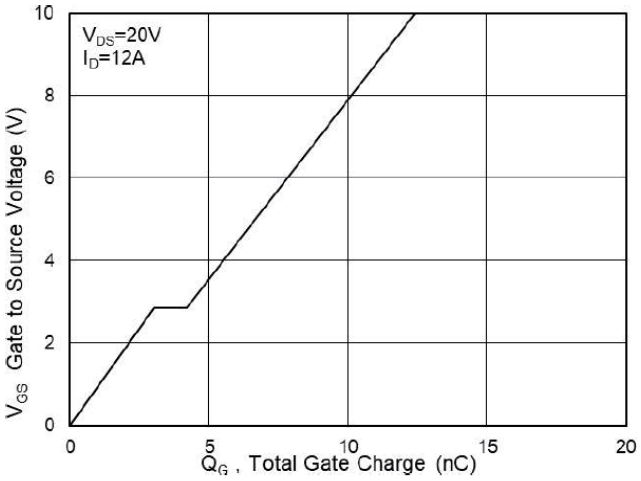


Figure 5: Normalized VGS(th) vs TJ

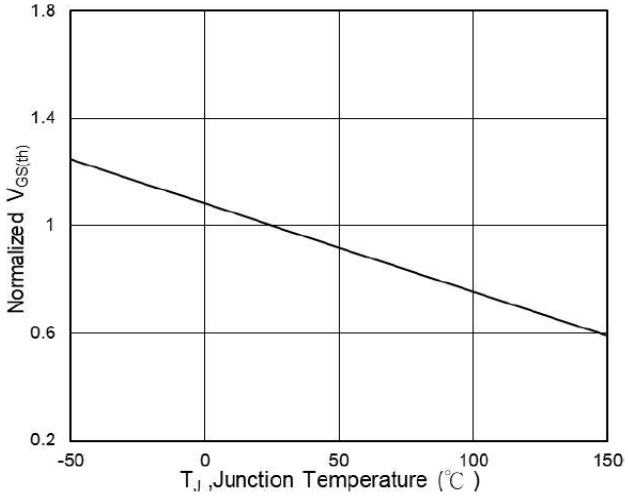
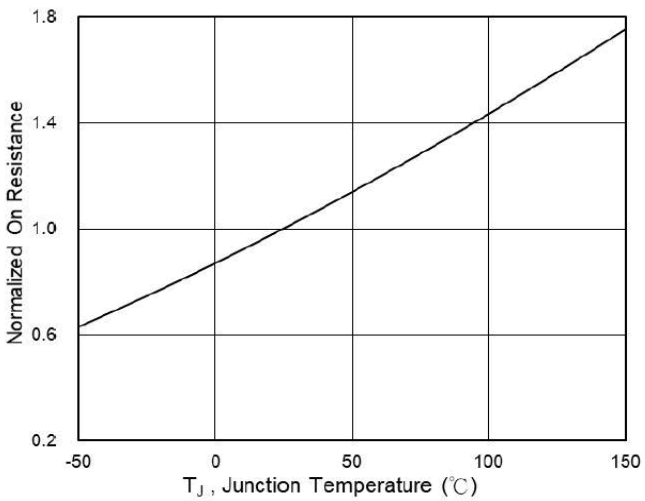


Figure 6:Normalized RDSON vs TJ



Typical Performance Characteristics

Figure 7:Capacitance

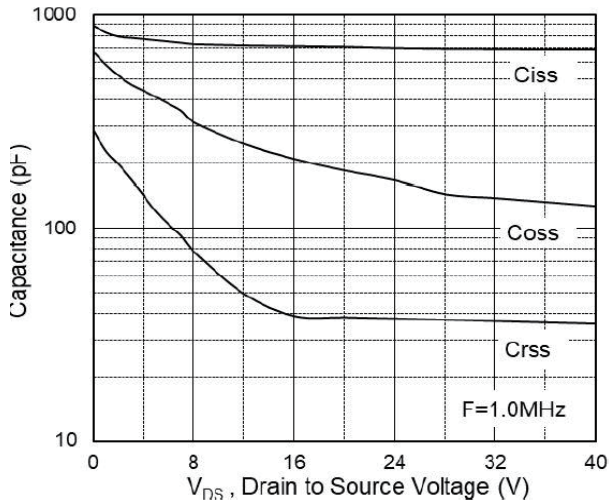


Figure 8: Safe Operating Area

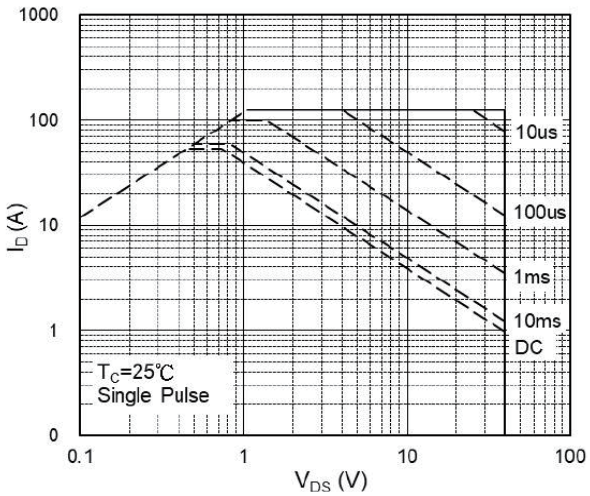


Figure 9:Normalized Maximum Transient

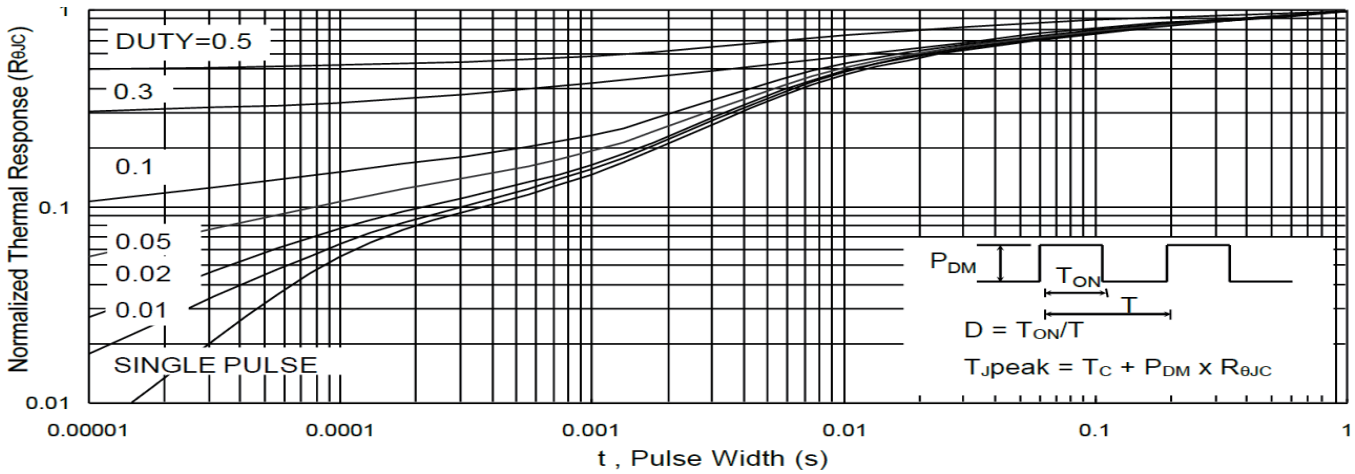


Figure 10:Switching Time W aveform

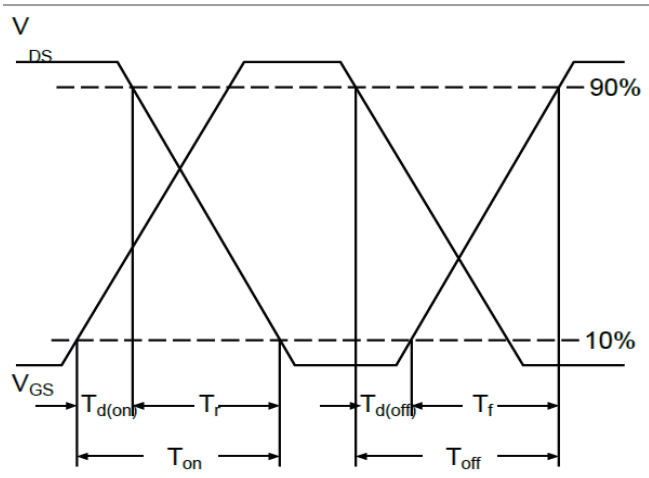
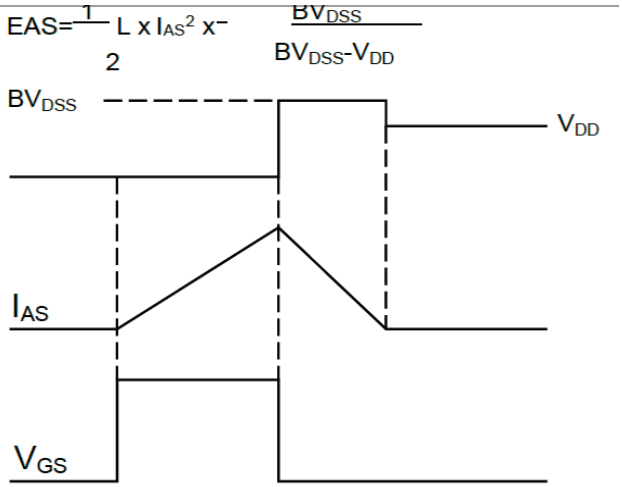
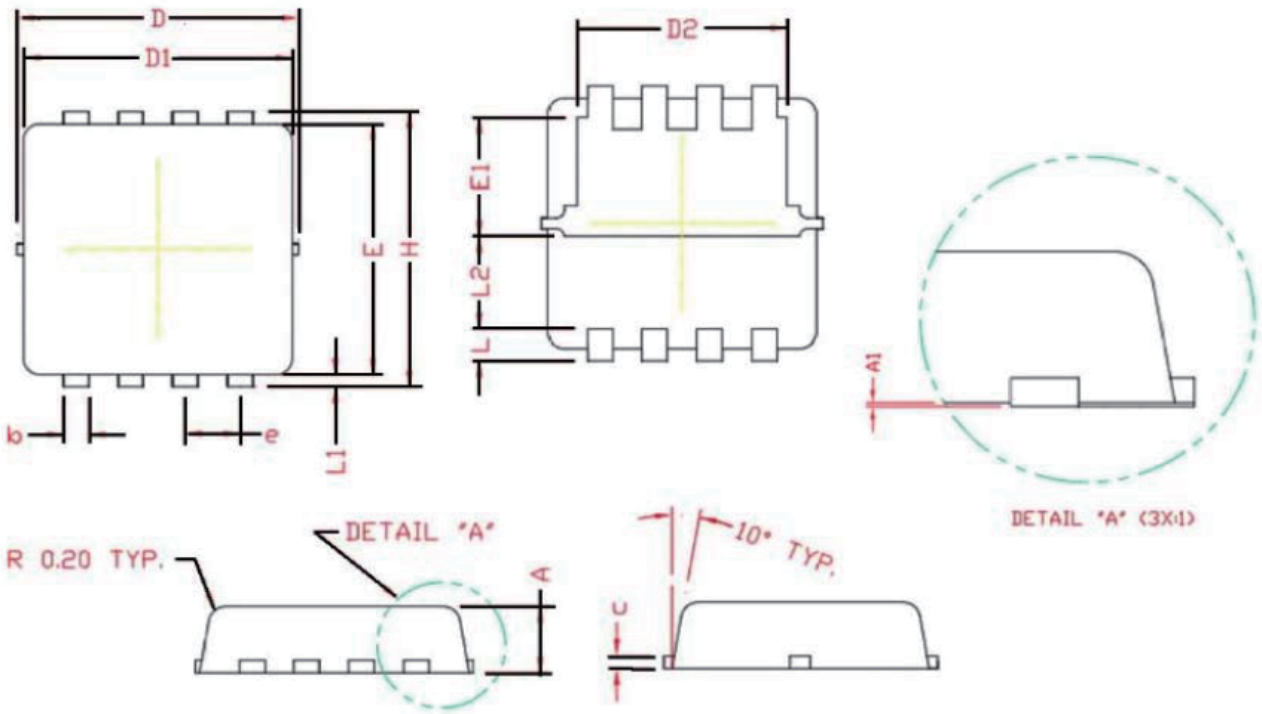


Figure 11: Unclamped Inductive Wavefor



PDFN3*3-8L Package Information



COMMON DIMENSIONS

(UNITS OF MEASURE=MILLIMETER)

SYMBOL	MIN	NOM	MAX
A	0.70	0.80	0.90
A1	0.00	0.03	0.05
b	0.24	0.30	0.35
c	0.10	0.15	0.20
D	3.25	3.32	3.40
D1	3.05	3.15	3.25
D2	2.40	2.50	2.60
E	3.00	3.10	3.20
E1	1.35	1.45	1.55
e	0.65 BSC.		
H	3.20	3.30	3.40
L	0.30	0.40	0.50
L1	0.10	0.15	0.20
L2	1.13 REF.		